## SN65C3222, SN75C3222 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS534B - MAY 2002 - REVISED OCTOBER 2004

- Operates With 3-V to 5.5-V V<sub>CC</sub> Supply
- Operates Up To 1 Mbit/s
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Applications
  - Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment

#### (TOP VIEW) 20 PWRDOWN FΝΓ C1+[]2 19 🛮 V<sub>CC</sub> 18 GND V+[]3 C1−∏4 17 DOUT1 16 **∏** RIN1 C2+∏5 C2- $\Pi$ 6 15 **∏** ROUT1 V−**∏** 7 14 NC DOUT2 8 13 DIN1 RIN2 I 9 12 **∏** DIN2 ROUT2 ¶ 10 ∏ NC

DB, DW, OR PW PACKAGE

NC - No internal connection

## description/ordering information

The SN65C3222 and SN75C3222 consist of two line drivers, two line receivers, and a dual charge-pump circuit with  $\pm 15$ -kV ESD protection pin to pin (serial-port connection pins, including GND). The devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/ $\mu$ s to 150 V/ $\mu$ s.

The SN65C3222 and SN75C3222 can be placed in the power-down mode by setting  $\overline{PWRDOWN}$  low, which draws only 1  $\mu$ A from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled, V+ is lowered to V<sub>CC</sub>, and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting  $\overline{EN}$  high.

#### ORDERING INFORMATION

TA	PACKAG	iņ	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	0010 (D)40	Tube of 25	SN75C3222DW	7500000
	SOIC (DW)	Reel of 2000	SN75C3222DWR	75C3222
−0°C to 70°C	SSOP (DB)	Reel of 2000	PART NUMBER e of 25 SN75C3222DW el of 2000 SN75C3222DWR el of 2000 SN75C3222DBR e of 70 SN75C3222PW el of 2000 SN75C3222PW el of 2000 SN75C3222DWR e of 25 SN65C3222DW el of 2000 SN65C3222DWR el of 2000 SN65C3222DBR el of 70 SN65C3222PW	CA3222
	TSSOP (PW)	Tube of 70	SN75C3222PW	CA2000
		Reel of 2000	SN75C3222PWR	CA3222
	COIC (DW)	Tube of 25	SN65C3222DW	0500000
	SOIC (DW)	Reel of 2000	PART NUMBER 25 SN75C3222DW 2000 SN75C3222DWR 2000 SN75C3222DBR 70 SN75C3222PW 2000 SN75C3222PW 2000 SN75C3222PWR 25 SN65C3222DW 2000 SN65C3222DWR 2000 SN65C3222DWR 2000 SN65C3222DBR 70 SN65C3222PW	65C3222
-40°C to 85°C	SSOP (DB)	Reel of 2000	SN65C3222DBR	CB3222
	TCCOD (DIA)	Tube of 70	SN65C3222PW	CDagge
	TSSOP (PW)	Reel of 2000	SN65C3222PWR	CB3222

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



#### **Function Tables**

## **EACH DRIVER**

IN	INPUTS DIN PWRDOWN					
DIN						
Х	L	Z				
L	Н	Н				
Н	Н	L				

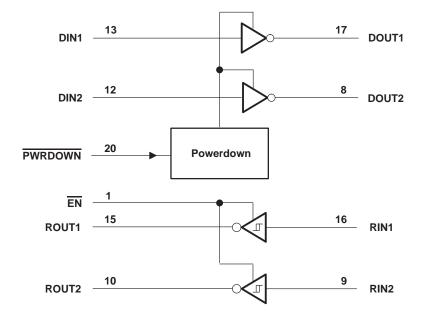
H = high level, L = low level, X = irrelevant, Z = high impedance

#### **EACH RECEIVER**

INPU	OUTPUT	
RIN	EN	ROUT
L	L	Н
Н	L	L
Χ	Н	Z
Open	L	Н

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

## logic diagram (positive logic)



## SN65C3222, SN75C3222 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS534B - MAY 2002 - REVISED OCTOBER 2004

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)	–0.3 V to 7 V
Negative output supply voltage range, V- (see Note 1)	0.3 V to -7 V
Supply voltage difference, V+ – V– (see Note 1)	13 V
Input voltage range, V <sub>I</sub> : Drivers, EN, PWRDOWN	0.3 V to 6 V
Receivers	–25 V to 25 V
Output voltage range, VO: Drivers	13.2 V to 13.2 V
Receivers	$\dots$ -0.3 V to V <sub>CC</sub> + 0.3 V
Package thermal impedance, θ <sub>JA</sub> (see Notes 2 and 3): DB package	
DW package	58°C/W
PW package	83°C/W
Operating virtual junction temperature, T <sub>J</sub>	150°C
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

- 2. Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is P<sub>D</sub> = (T<sub>J</sub>(max) T<sub>A</sub>)/θ<sub>JA</sub>. Operating at the absolute maximum T<sub>J</sub> of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

## recommended operating conditions (see Note 4 and Figure 5)

				MIN	NOM	MAX	UNIT
	Owner houselfer me	V <sub>CC</sub> = 3.3 V		3	3.3	3.6	.,
	Supply voltage	V <sub>CC</sub> = 5 V		4.5	5	5.5	V
V <sub>IH</sub>	Britan and an abrillian bould and an in-	DIN EN BWBBOWN	V <sub>CC</sub> = 3.3 V	2			.,
	Driver and control high-level input voltage	DIN, EN, PWRDOWN	V <sub>CC</sub> = 5 V	2.4			V
VIL	Driver and control low-level input voltage	DIN, EN, PWRDOWN				8.0	V
٧ <sub>I</sub>	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
٧ <sub>I</sub>	Receiver input voltage			-25		25	V
т.	Operating free circumperature	SN65C3222	_	-40		85	°C
TA	Operating free-air temperature	SN75C3222	SN75C3222			70	C

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
II	Input leakage current (EN, PWRDOWN)			±0.01	±1	μΑ
Ī	Supply current	No load, PWRDOWN at VCC		0.3	1	mA
ICC	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μΑ

<sup>‡</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V $_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V $_{CC}$  = 5 V  $\pm$  0.5 V.



#### **DRIVER SECTION**

## electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER TEST CONDITIONS				MIN	TYP	MAX	UNIT
Vон	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		V
VOL	Low-level output voltage	DOUT at R <sub>L</sub> = $3 \text{ k}\Omega$ to GND,	DIN = V <sub>CC</sub>	-5	-5.4		V
lιΗ	High-level input current	VI = VCC			±0.01	±1	μΑ
IIL	Low-level input current	V <sub>I</sub> at GND			±0.01	±1	μΑ
	Object along the standard assessed	V <sub>CC</sub> = 3.6 V,	VO = 0 V		±35	±60	A
los	Short-circuit output current‡	$V_{CC} = 5.5 \text{ V},$	VO = 0 V		±35	±90	mA
r <sub>O</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	$V_O = \pm 2 V$	300	10M		Ω
1	Output leakage current	PWRDOWN = GND	$V_O = \pm 12 \text{ V},  V_{CC} = 3 \text{ V to } 3.6 \text{ V}$			±25	
loff		FVVKDOVVIN = GND	$V_O = \pm 10 \text{ V},  V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$			±25	μΑ

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

## switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER		TEST CONDITIONS				MAX	UNIT
Maximum data rate (see Figure 1)			C <sub>L</sub> = 1000 pF		250			
		$R_L = 3 k\Omega$ , One DOUT switching	C <sub>L</sub> = 250 pF,	$V_{CC} = 3 V \text{ to } 4.5 V$	1000			kbit/s
		ono Boot ownorming	C <sub>L</sub> = 1000 pF,	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	1000			
t <sub>sk(p)</sub>	Pulse skew§	C <sub>L</sub> = 150 pF to 2500 pF	$R_L$ = 3 kΩ to 7 kΩ, See Figure 2			300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	R <sub>L</sub> = 3 kΩ to 7 kΩ, V <sub>CC</sub> = 3.3 V	C <sub>L</sub> = 150 pF to 100	00 pF	18		150	V/μs

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

§ Pulse skew is defined as  $|tp_{LH} - tp_{HL}|$  of each channel of the same device. NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.



<sup>‡</sup> Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

SLLS534B - MAY 2002 - REVISED OCTOBER 2004

#### RECEIVER SECTION

#### electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> – 0.6 V	V <sub>CC</sub> – 0.1 V		V
VOL	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
V <sub>IT+</sub>	Decitive asing input threshold voltage	V <sub>CC</sub> = 3.3 V		1.5	2.4	V
	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.8	2.4	V
V	No notive point in a taken a lateral	V <sub>CC</sub> = 3.3 V	0.6	1.2		.,
VIT-	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.8	1.5		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.3		V
loff	Output leakage current	EN = V <sub>CC</sub>		±0.05	±10	μΑ
rį	Input resistance	$V_{I} = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

† All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C. NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V  $\pm$  0.5 V.

#### switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST CONDITIONS	MIN TYPT	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	$C_{L} = 150$ pF, See Figure 3		ns	
tPHL	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF, See Figure 3	300		ns
t <sub>en</sub>	Output enable time	$C_L$ = 150 pF, $R_L$ = 3 kΩ, See Figure 4	200		ns
t <sub>dis</sub>	Output disable time	$C_L$ = 150 pF, $R_L$ = 3 kΩ, See Figure 4	200		ns
t <sub>sk(p)</sub>	Pulse skew <sup>‡</sup>	See Figure 3	300		ns

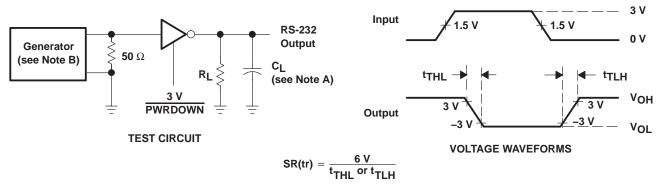
<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.



<sup>‡</sup> Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

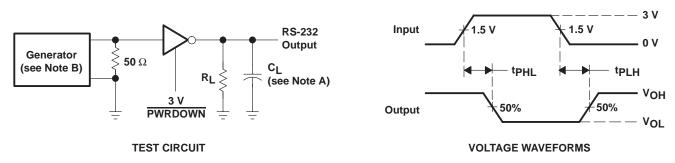
#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50~\Omega$ , 50% duty cycle,  $t_\Gamma \le 10$  ns.  $t_f \le 10$  ns.

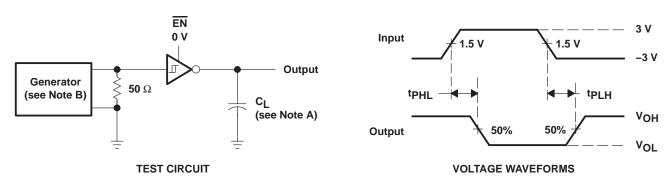
Figure 1. Driver Slew Rate



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.

Figure 2. Driver Pulse Skew



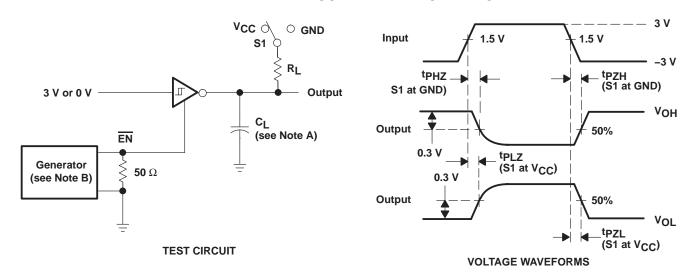
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 3. Receiver Propagation-Delay Times



#### PARAMETER MEASUREMENT INFORMATION

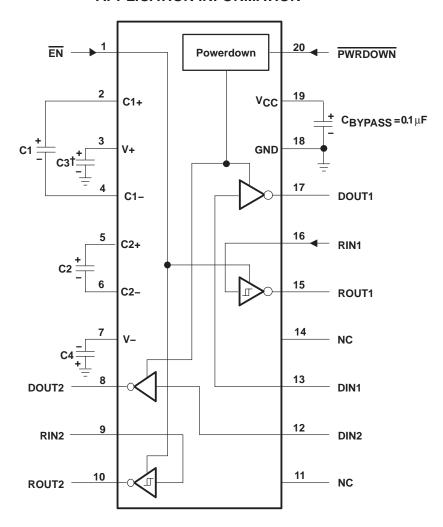


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50 \ \Omega$ , 50% duty cycle,  $t_\Gamma \le 10 \ ns$ ,  $t_f \le 10 \ ns$ .

Figure 4. Receiver Enable and Disable Times

## **APPLICATION INFORMATION**



 $^\dagger\text{C3}$  can be connected to  $\text{V}_{\mbox{CC}}$  or GND.

NOTES: A. Resistor values shown are nominal.

B. NC - No internal connection

## V<sub>CC</sub> vs CAPACITOR VALUES

v <sub>cc</sub>	C1	C2, C3, and C4
3.3 V $\pm$ 0.3 V	<b>0.1</b> μ <b>F</b>	<b>0.1</b> μ <b>F</b>
5 V ± 0.5 V	<b>0.047</b> μ <b>F</b>	<b>0.33</b> μF
3 V to 5.5 V	<b>0.1</b> μ <b>F</b>	<b>0.47</b> μ <b>F</b>

Figure 5. Typical Operating Circuit and Capacitor Values



www.ti.com 11-Nov-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
SN65C3222DBR	Active	Production	SSOP (DB)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222
SN65C3222DBR.A	Active	Production	SSOP (DB)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3222
SN65C3222DWR	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222
SN65C3222DWR.A	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222
SN65C3222PW	Obsolete	Production	TSSOP (PW)   20	-	-	Call TI	Call TI	-40 to 85	CB3222
SN75C3222DW	Active	Production	SOIC (DW)   20	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222
SN75C3222DW.A	Active	Production	SOIC (DW)   20	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222
SN75C3222DWR	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222
SN75C3222DWR.A	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3222
SN75C3222PW	Obsolete	Production	TSSOP (PW)   20	-	-	Call TI	Call TI	0 to 70	CA3222

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



## PACKAGE OPTION ADDENDUM

www.ti.com 11-Nov-2025

and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

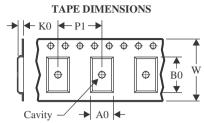
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 24-Jul-2025

## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

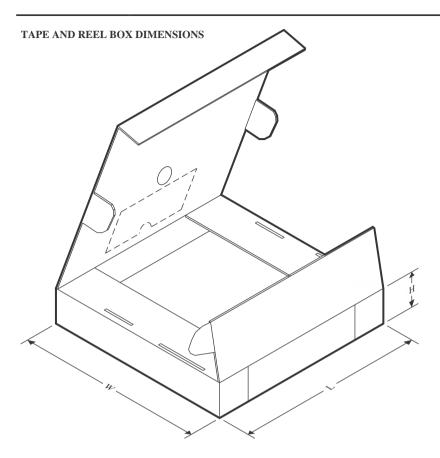
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75C3222DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

www.ti.com 24-Jul-2025



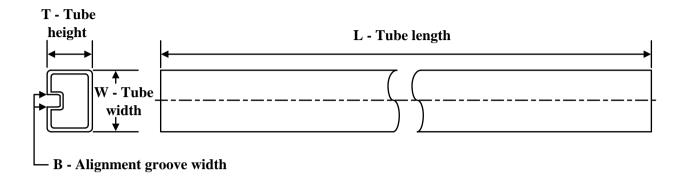
#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222DBR	SSOP	DB	20	2000	353.0	353.0	32.0
SN65C3222DWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN75C3222DWR	SOIC	DW	20	2000	356.0	356.0	45.0

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 24-Jul-2025

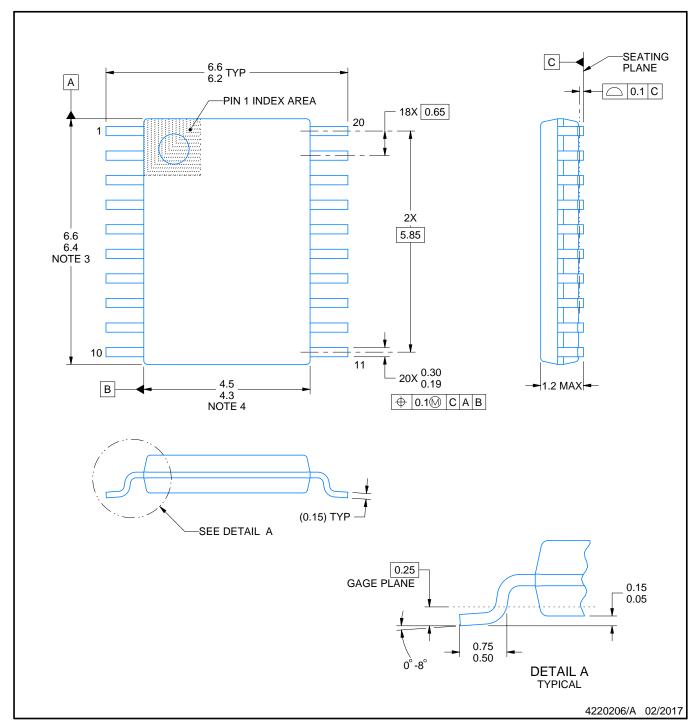
## **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN75C3222DW	DW	SOIC	20	25	507	12.83	5080	6.6
SN75C3222DW.A	DW	SOIC	20	25	507	12.83	5080	6.6





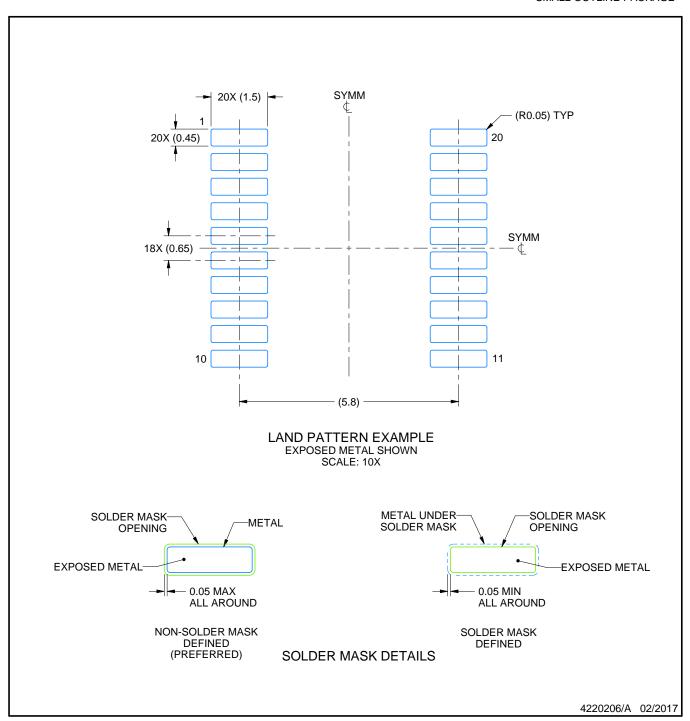
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



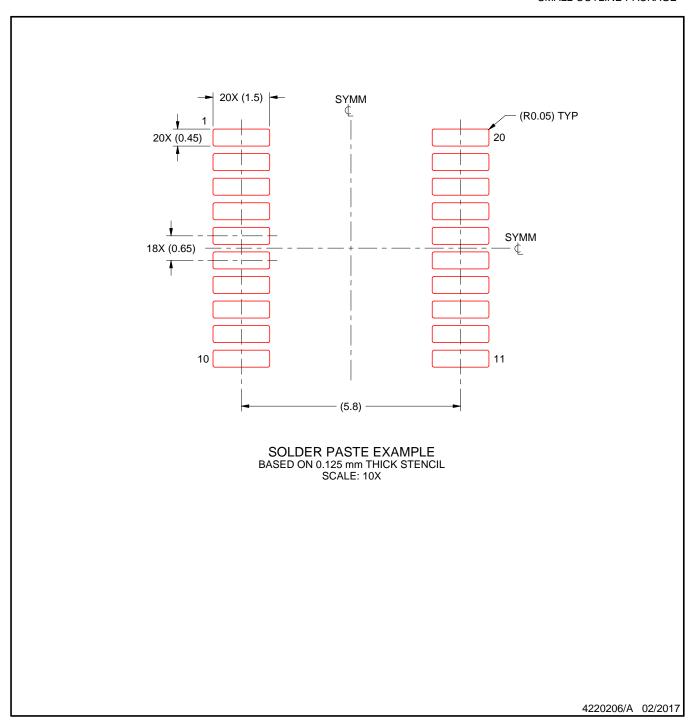


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



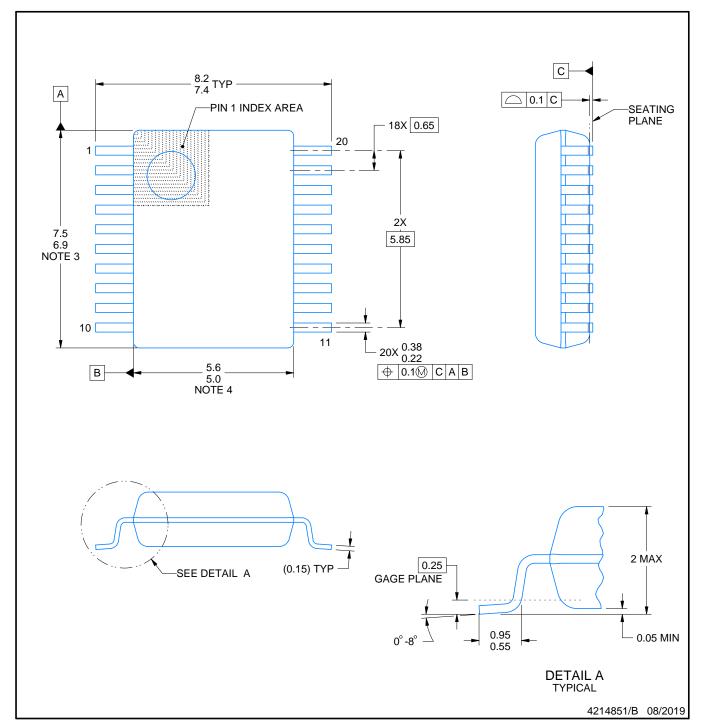


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







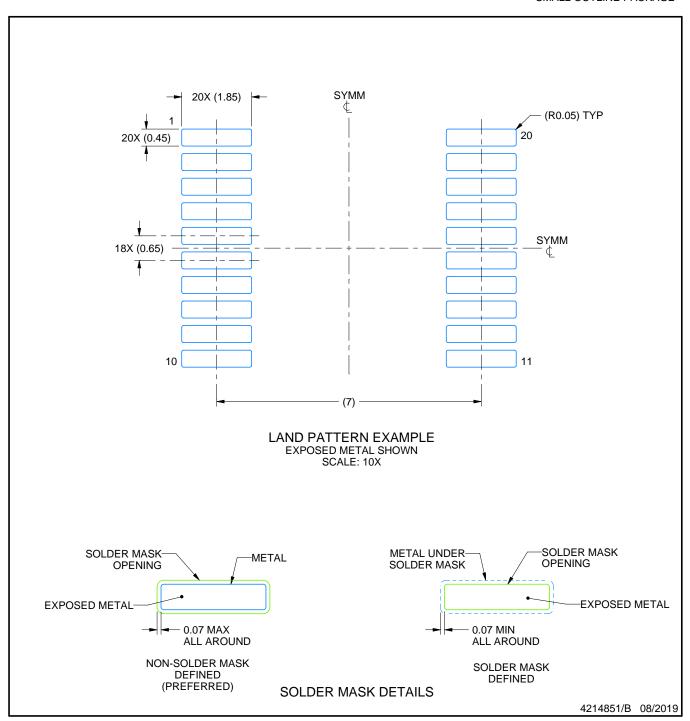
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



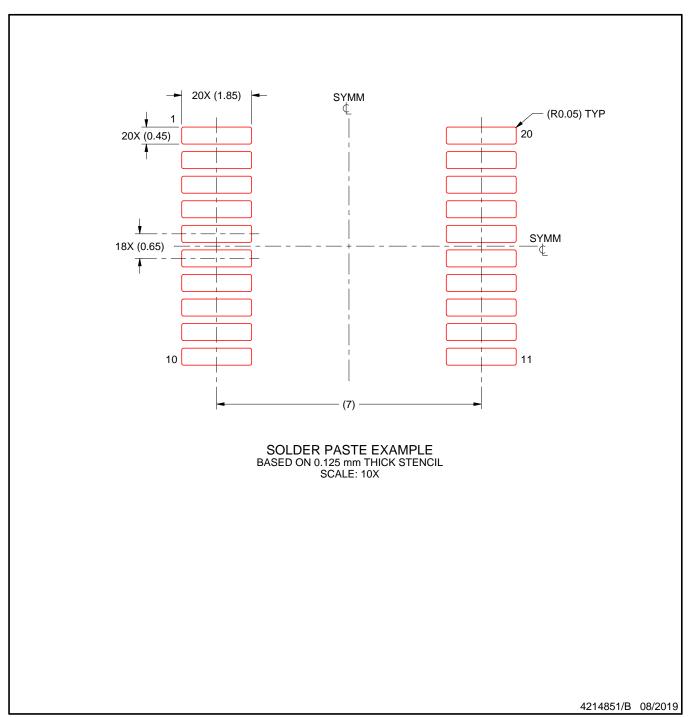


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SOIC



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025